N-Channel Enhancement Mode Power MOSFET

Description

The GT035N10MA uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

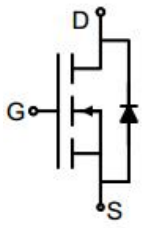
AEC-Q101 Qualified

General Features

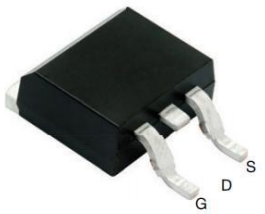
- V_{DS} 100V
- I_D (at V_{GS} = 10V) 190A
- $R_{DS(ON)}$ (at V_{GS} = 10V) < 3.5mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-263

Ordering Information

Device	Package	Marking	Packaging
GT035N10MA	TO-263	GT035N10	800pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	100	V
Continuous Drain Current (Silicon limit)	T_C = 25℃	I_D	210	A
Continuous Drain Current (Package limit)	T_C = 25℃		190	
Continuous Drain Current (Package limit)	T_C = 100℃		120	
Pulsed Drain Current (note1)		I_{DM}	760	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation	T_C = 25℃	P_D	277	W
	T_C = 100℃		111	
Single pulse avalanche energy （note2）		E_{AS}	441	mJ
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 To 175	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	55	ºC/W
Maximum Junction-to-Case	R_{thJC}	0.45	ºC/W

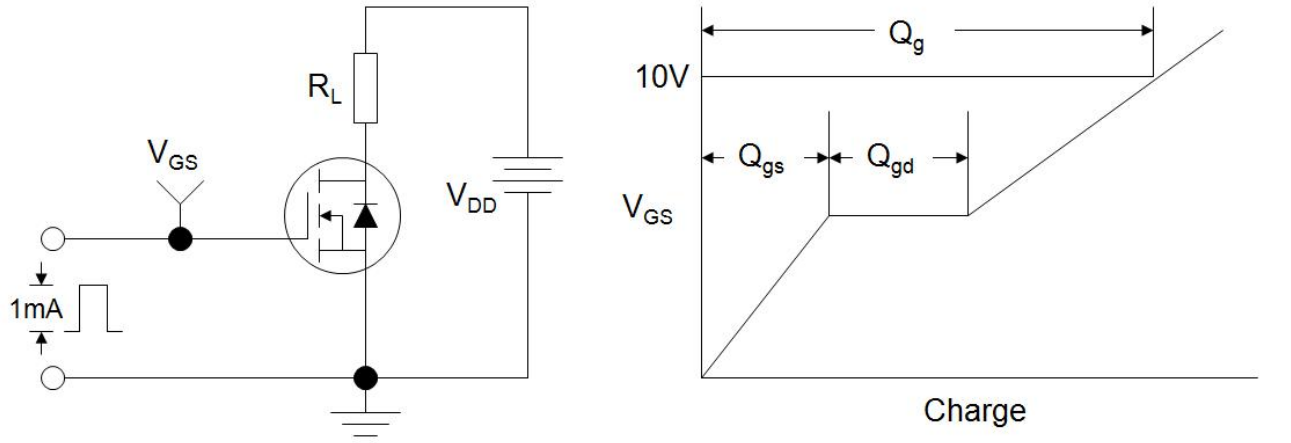
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100V, V_{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	3	4	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 20A	--	2.9	3.5	mΩ
		V_{GS} = 10V, I_D = 20A, T_C = 100℃	--	3.9	4.8	
Gate Resistance	R_g	V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz	--	2.5	--	Ω
Forward Transconductance	g_{FS}	V_{GS} = 5V, I_D = 20A	--	51	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1.0MHz	--	6188	--	pF
Output Capacitance	C_{oss}		--	1928	--	
Reverse Transfer Capacitance	C_{rss}		--	178	--	
Total Gate Charge	Q_g	V_{DD} = 50V, I_D = 50A, V_{GS} = 10V	--	68	--	nC
Gate-Source Charge	Q_{gs}		--	26	--	
Gate-Drain Charge	Q_{gd}		--	31	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 50V, I_D = 50A, R_G = 3Ω	--	27	--	ns
Turn-on Rise Time	t_r		--	21	--	
Turn-off Delay Time	$t_{d(off)}$		--	78	--	
Turn-off Fall Time	t_f		--	30	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	190	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 20A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Qrr	I_F = 20A, V_{GS} = 0V di/dt=100A/us	--	680	--	nC
Reverse Recovery Time	Trr		--	132	--	ns

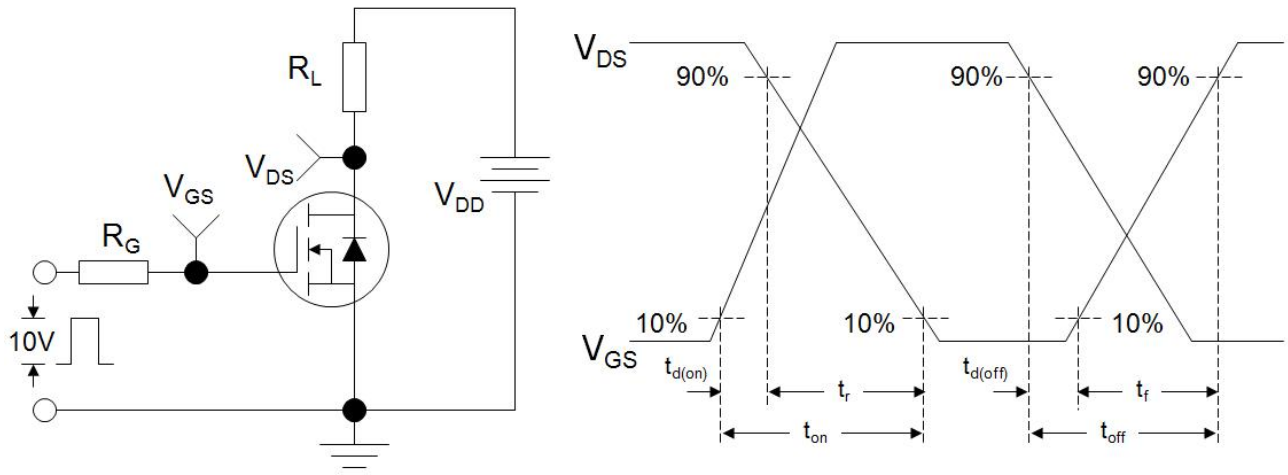
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=50V,VGS=10V,L=0.5mH,Rg=25Ω
3. Identical low side and high side switch with identical R_G

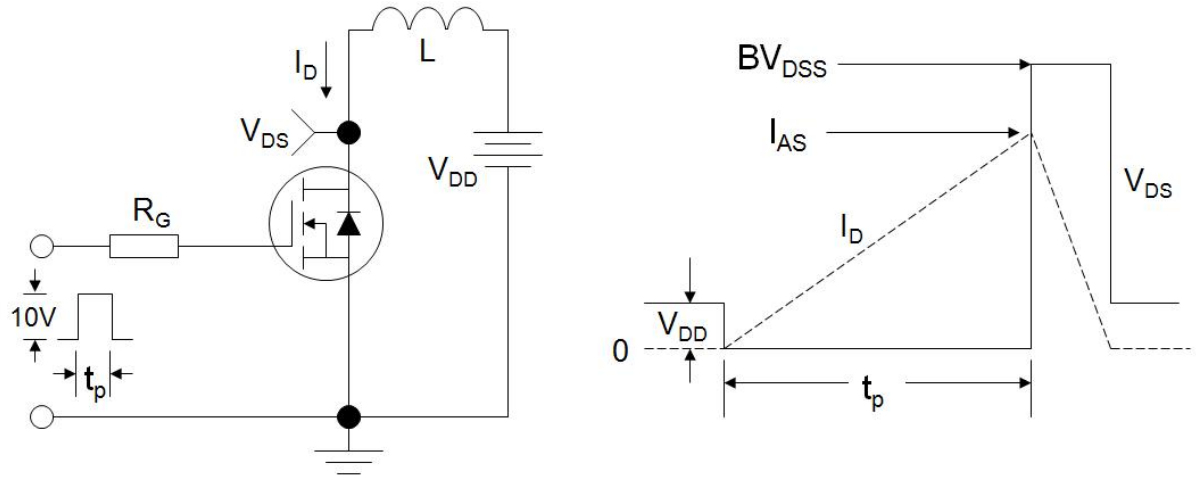
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

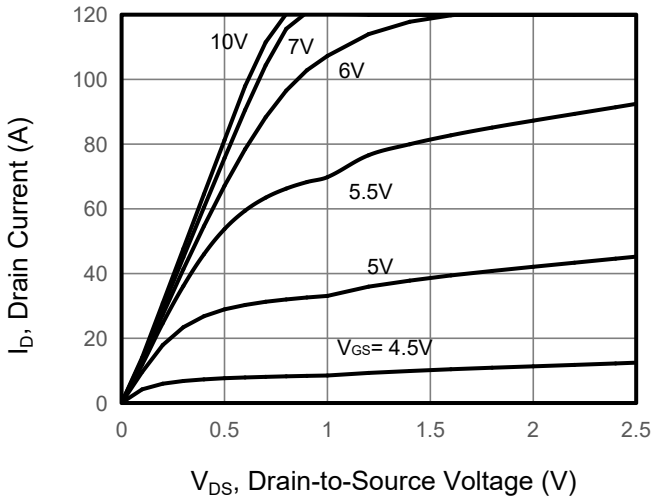


Figure 2. Transfer Characteristics

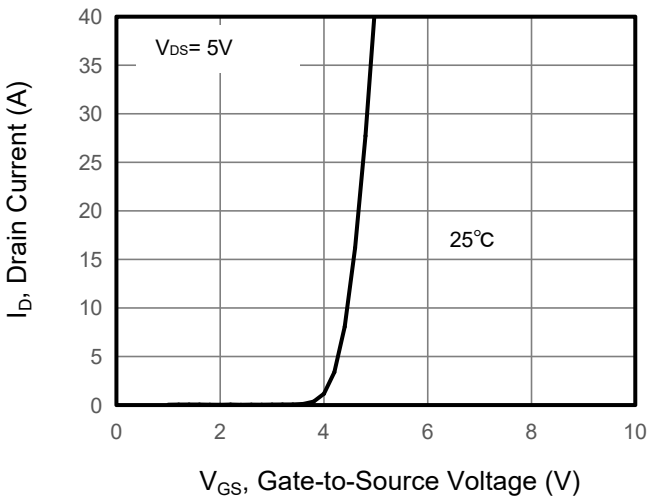


Figure 3. Drain Source On Resistance

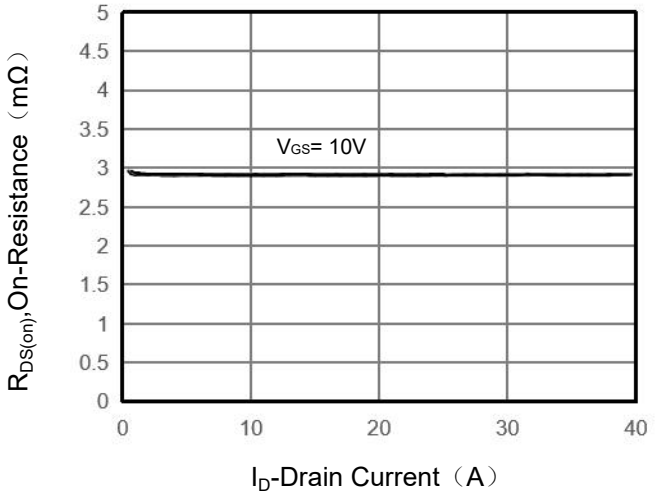


Figure 4. Gate Charge

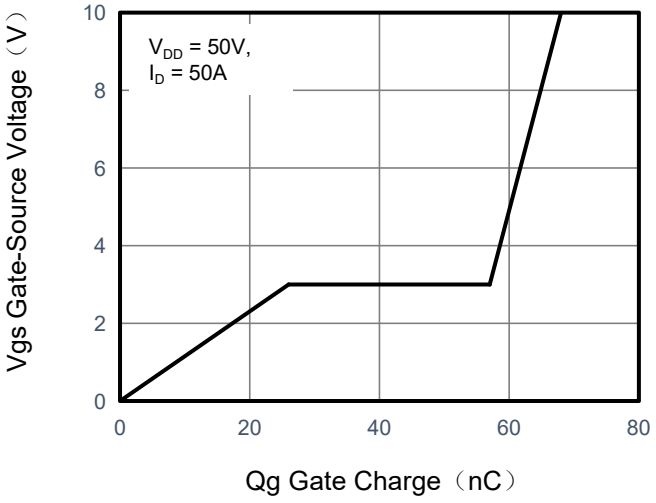


Figure 5. Capacitance

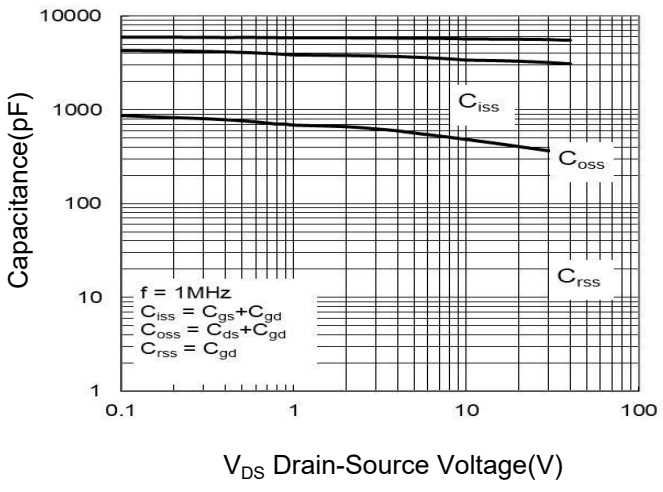
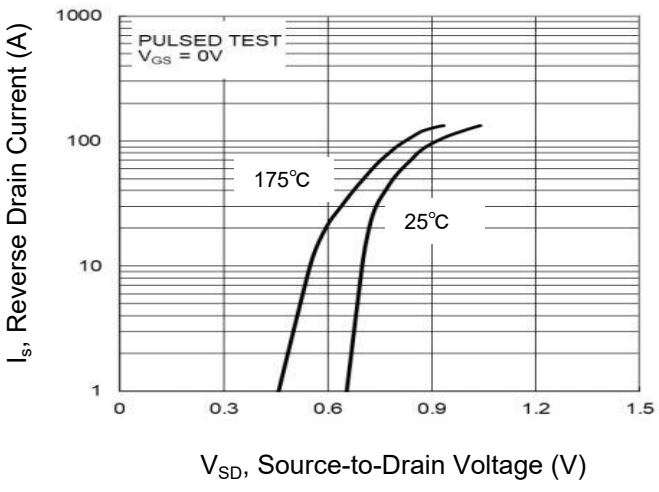


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

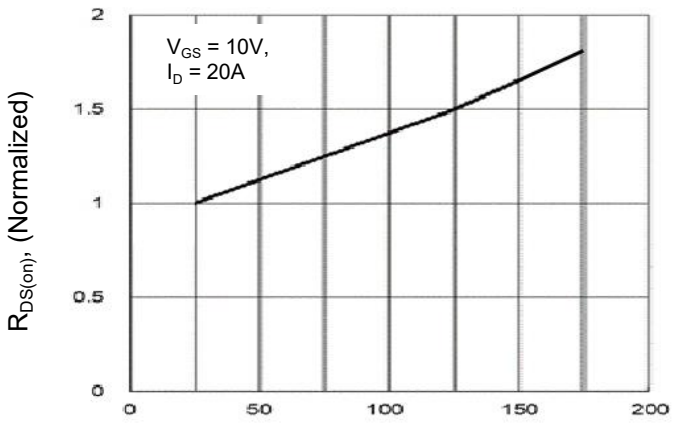


Figure 8. Safe Operation Area

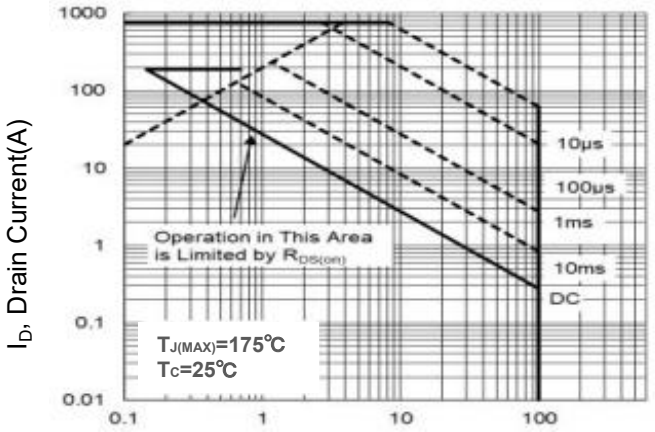
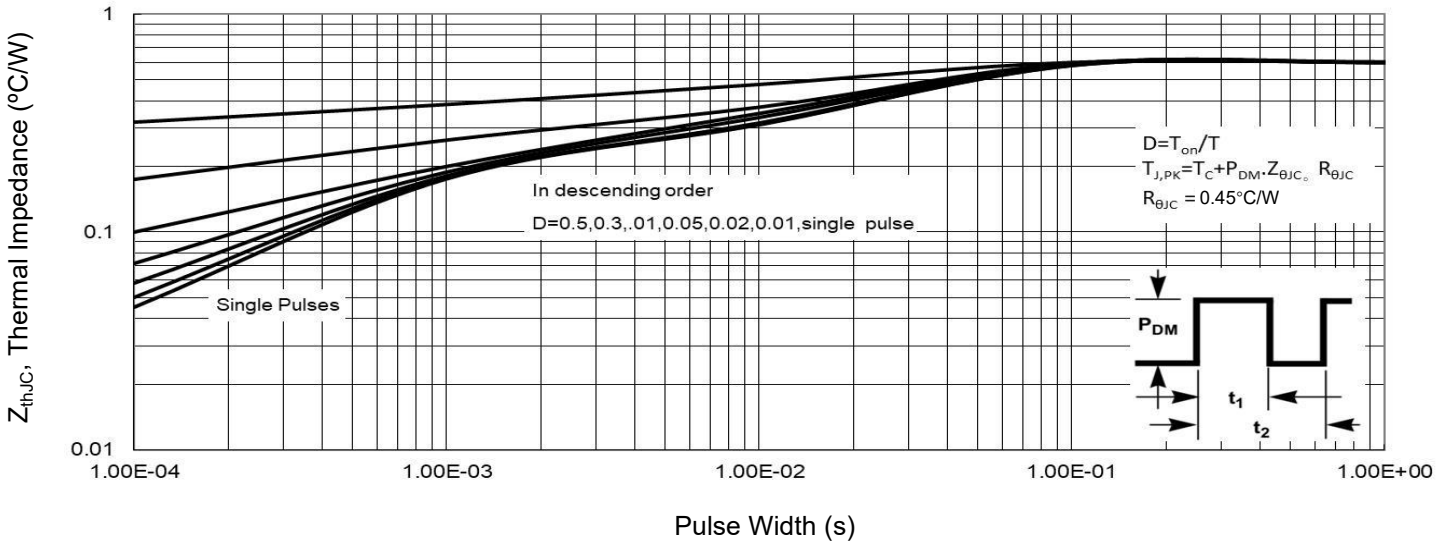
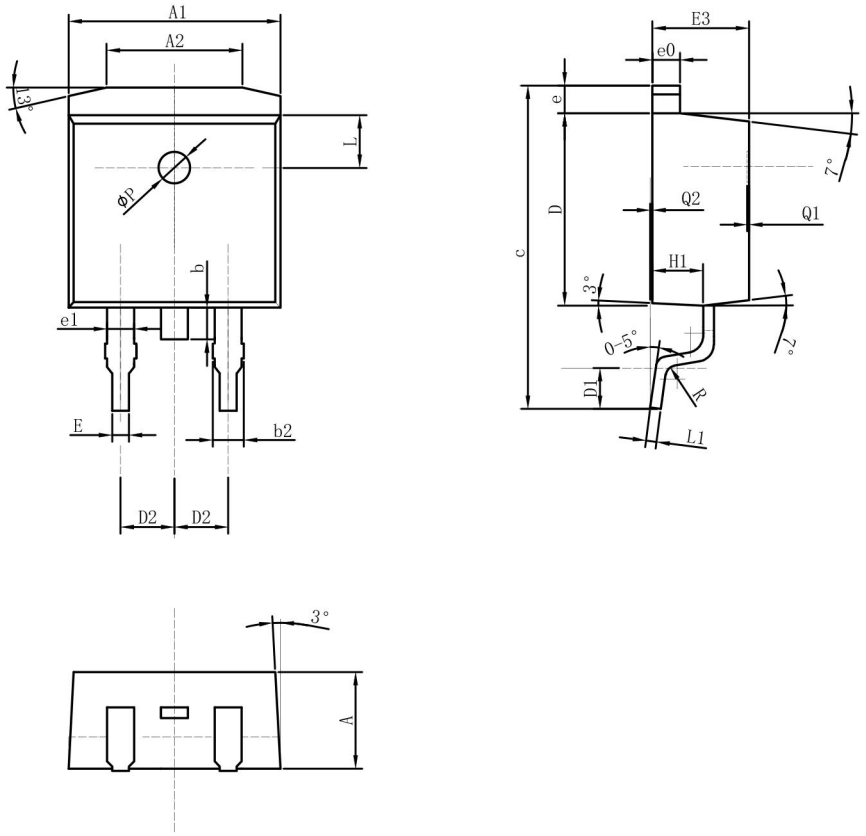


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-263 Package Information



COMMON DIMENSIONS

SYMBO	mm		
	MIN	NOM	MAX
A	4.52	4.57	4.62
A1	9.95	10.00	10.05
A2	6.30	6.40	6.50
b	1.30	1.50	1.70
b2	1.17	1.27	1.37
c	14.80	15.00	15.20
D	9.05	9.10	9.15
D1	1.90	2.10	2.30
D2	-	2.54	-
E	-	0.80	-
E3	-	4.57	-
e	-	1.30	-
e0	-	1.30	-
e1	1.73	3	-
H1	-	2.40	-
L	-	2.50	-
L1	-	0.50	-
ΦP	-	1.50	-
R	-	0.50	-
Q1	0.10	-	0.15
Q2	0	-	0.02